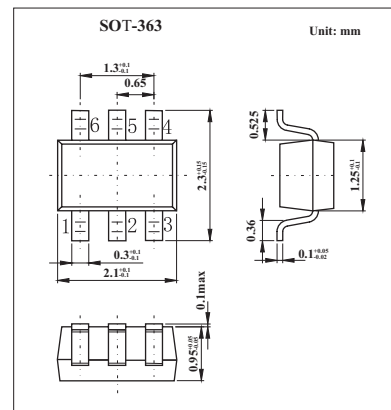


Schottky Barrier Diodes

1PS88SB48

■ Features

- Ultra fast switching speed
- Low forward voltage
- Small SMD package
- Guard ring protected
- Absorbs very high surge pulse
- Low capacitance.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
continuous reverse voltage	V_R			40	V
continuous forward current	I_F			120	mA
repetitive peak forward current	I_{FRM}	$t_p \leq 1 \text{ s}; \delta \leq 0.5$		120	mA
non-repetitive peak forward current	I_{FSM}	$t_p < 10 \text{ ms}$		200	mA
storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
junction temperature	T_j			150	$^\circ\text{C}$
operating ambient temperature	T_{amb}		-65	+150	$^\circ\text{C}$
thermal resistance from junction to ambient	R_{th-j-a}			416	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Max	Unit
continuous forward voltage	V_F	$I_F = 1 \text{ mA}$	380	mV
		$I_F = 10 \text{ mA}$	500	mV
		$I_F = 40 \text{ mA}$	1	V
continuous reverse current	I_R	$V_R = 30 \text{ V}$	1	μA
		$V_R = 80 \text{ V}$	10	μA
diode capacitance	C_T	$V_R=0 \text{ V}, f=1 \text{ MHz}$	5	pF

Note

1. Pulse test: $t_p = 300 \mu\text{ s}; \delta = 0.02$.

■ Marking

Marking	8t5
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